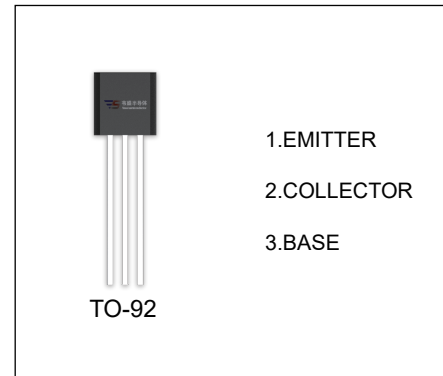


2N4126 TRANSISTOR (PNP)

FEATURES

- PNP Silicon Epitaxial Transistor for Switching and Amplifier Applications.
- As Complementary Type, The NPN Transistor 2N4124 is Recommended.



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2N4126	TO-92	Bulk	1000pcs/Bag
2N4126-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-25	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-4	V
I _C	Collector Current -Continuous	-0.2	A
P _D	Collector Power Dissipation	625	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	200	°C /W
T _J , T _{stg}	Junction Temperature	-55~+150	°C

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.01\text{mA}, I_E = 0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.01\text{mA}, I_C = 0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20\text{V}, I_E = 0$			-50	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$			-50	nA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1\text{V}, I_C = -2\text{mA}$	120		360	
	$h_{FE(2)}$	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-0.95	V
Collector output capacitance	C_{ob}	$V_{CB} = -5\text{V}, I_E = 0, f = 1\text{MHz}$			4.5	pF
Transition frequency	f_T	$V_{CE} = -20\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$	250			MHz

 *Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 1.5\%$.